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	NTI-029	10/005,615
	Applicant	
	CHANG, Fang-Cheng	
	Filing Date	Group
	11/7/2001	2825

U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
W	6,014,456	1/11/2000	Tsudaka	382	144	7/15/1996
	6,154,563	11/28/2000	Tsudaka	382	144	12/17/1998
	6,298,473 B1	10/2/2001	Ono, et al.	716	21	12/3/1998
	6,338,922 B1	1/15/2002	Liebinann, et al.	430	5	5/8/2000
	6,453,457 B1	9/17/2002	Pierrat, et al.	716	19	9/29/2000
	2002/0100004 A1	7/25/2002	Pierrat, et al.	716	5	3/15/2002

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INFORMATION DISCLOSURE CITATION PTO-1449		Att'y. Docket No. NTI-029	Serial No. 10/005,615
		Applicant CHANG, Fang-Cheng	
		Filing Date 11/7/2001	Group 2825
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W	Kirk, J., "Measurement of Astigmatism in Microlithography Lenses", IBM Microelectronics (7 pages).		
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	5,682,323	10/28/1997	Pasch, et al.	364	491	3/6/1995
	5,723,233	3/3/1998	Garza, et al.	430	5	2/27/1996
	5,801,954	9/1/1998	Le, et al.	364	488	4/24/1996
	5,815,685	9/29/1998	Kamon	395	500	9/15/1995
	5,825,647	10/20/1998	Tsudaka	364	167.03	3/12/1996
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	6,049,789	4/11/2000	Frison, et al.	705	59	6/24/1998
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	6,081,659	6/27/2000	Garza, et al.	395	500.22	4/26/1999
	6,289,499	9/11/2001	Rieger, et al.	716	21	1/7/2000
	6,243,855 B1	6/5/2001	Kobayashi, et al.	716	19	9/29/1998
	6,249,597 B1	6/19/2001	Tsudaka	382	144	12/17/1998

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EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
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	WO 00/67075 A1	11/9/2000	WO			<input type="checkbox"/>	<input type="checkbox"/>
	WO 00/67076 A1	11/9/2000	WO			<input type="checkbox"/>	<input type="checkbox"/>
	GB 2,324,169 A	10/14/1998	GB			<input type="checkbox"/>	<input type="checkbox"/>
	WO 99/14638 A1	3/25/1999	WO			<input type="checkbox"/>	<input type="checkbox"/>

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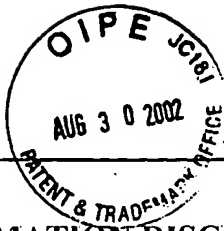
INFORMATION DISCLOSURE CITATION PTO-1449	Atty. Docket No. NTI-029	Serial No. 10/005,615-9717
	Applicant CHANG, Fang-Cheng	Group 2825
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